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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	18432
Number of I/O	91
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p060-tqg144i

I/Os Per Package ¹

ProASIC3 Devices	A3P015 ²	A3P030	A3P060	A3P125	A3P250 ³		A3P400 ³		A3P600		A3P1000	
Cortex-M1 Devices					M1A3P250 ^{3,5}		M1A3P400 ³		M1A3P600		M1A3P1000	
Package	I/O Type											
	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O ⁴	Differential I/O Pairs	Single-Ended I/O ⁴	Differential I/O Pairs	Single-Ended I/O ⁴	Differential I/O Pairs	Single-Ended I/O ⁴	Differential I/O Pairs
QN48	–	34	–	–	–	–		–	–	–	–	–
QN68	49	49	–	–	–	–	–	–		–	–	–
QN132 ⁷	–	81	80	84	87	19	–	–		–	–	–
CS121	–	–	96	–	–	–	–	–	–	–	–	–
VQ100	–	77	71	71	68	13	–	–		–	–	–
TQ144	–	–	91	100	–	–	–	–	–	–	–	–
PQ208	–	–	–	133	151	34	151	34	154	35	154	35
FG144	–	–	96	97	97	24	97	25	97	25	97	25
FG256 ^{5,6}	–	–	–	–	157	38	178	38	177	43	177	44
FG484 ⁶	–	–	–	–	–	–	194	38	235	60	300	74

Notes:

1. When considering migrating your design to a lower- or higher-density device, refer to the [ProASIC3 FPGA Fabric User Guide](#) to ensure complying with design and board migration requirements.
2. A3P015 is not recommended for new designs.
3. For A3P250 and A3P400 devices, the maximum number of LVPECL pairs in east and west banks cannot exceed 15. Refer to the [ProASIC3 FPGA Fabric Users Guide](#) for position assignments of the 15 LVPECL pairs.
4. Each used differential I/O pair reduces the number of single-ended I/Os available by two.
5. The M1A3P250 device does not support FG256 package.
6. FG256 and FG484 are footprint-compatible packages.
7. Package not available.

Table 1 • ProASIC3 FPGAs Package Sizes Dimensions

Package	CS121	QN48	QN68	QN132 *	VQ100	TQ144	PQ208	FG144	FG256	FG484
Length × Width (mm × mm)	6 × 6	6 × 6	8 × 8	8 × 8	14 × 14	20 × 20	28 × 28	13 × 13	17 × 17	23 × 23
Nominal Area (mm ²)	36	36	64	64	196	400	784	169	289	529
Pitch (mm)	0.5	0.4	0.4	0.5	0.5	0.5	0.5	1.0	1.0	1.0
Height (mm)	0.99	0.90	0.90	0.75	1.00	1.40	3.40	1.45	1.60	2.23

Note: * Package not available

RAM Contribution— P_{MEMORY}

$$P_{\text{MEMORY}} = P_{\text{AC11}} * N_{\text{BLOCKS}} * F_{\text{READ-CLOCK}} * \beta_2 + P_{\text{AC12}} * N_{\text{BLOCK}} * F_{\text{WRITE-CLOCK}} * \beta_3$$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{\text{READ-CLOCK}}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations.

$F_{\text{WRITE-CLOCK}}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in [Table 2-17 on page 2-14](#).

PLL Contribution— P_{PLL}

$$P_{\text{PLL}} = P_{\text{DC4}} + P_{\text{AC13}} * F_{\text{CLKOUT}}$$

F_{CLKOUT} is the output clock frequency.¹

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
 - Bit 0 (LSB) = 100%
 - Bit 1 = 50%
 - Bit 2 = 25%
 - ...
 - Bit 7 (MSB) = 0.78125%
 - Average toggle rate = (100% + 50% + 25% + 12.5% + ... + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-16 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 2-17 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

1. The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($P_{\text{AC14}} * F_{\text{CLKOUT}}$ product) to the total PLL contribution.

Table 2-20 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings
Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option ²	Slew Rate	VIL		VIH		VOL	VOH	IOL ¹ mA	IOH ¹ mA
				Min V	Max V	Min V	Max V	Max V	Min V		
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8 mA	High	−0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range ³	100 μ A	8 mA	High	−0.3	0.8	2	3.6	0.2	VCCI − 0.2	0.1	0.1
2.5 V LVCMOS	8 mA	8 mA	High	−0.3	0.7	1.7	2.7	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2

Notes:

1. Currents are measured at 85°C junction temperature.
2. 3.3 V LVCMOS wide range is applicable to 100 μ A drive strength only. The configuration will NOT operate at the equivalent software default drive strength. These values are for Normal Ranges ONLY.
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.

Table 2-21 • Summary of Maximum and Minimum DC Input Levels
Applicable to Commercial and Industrial Conditions

DC I/O Standards	Commercial ¹		Industrial ²	
	IIL ³	IIH ⁴	IIL ³	IIH ⁴
	μ A	μ A	μ A	μ A
3.3 V LVTTTL / 3.3 V LVCMOS	10	10	15	15
3.3 V LVCMOS Wide Range	10	10	15	15
2.5 V LVCMOS	10	10	15	15
1.8 V LVCMOS	10	10	15	15
1.5 V LVCMOS	10	10	15	15
3.3 V PCI	10	10	15	15
3.3 V PCI-X	10	10	15	15

Notes:

1. Commercial range (0°C < T_A < 70°C)
2. Industrial range (−40°C < T_A < 85°C)
3. IIL is the input leakage current per I/O pin over recommended operation conditions where −0.3V < V_{IN} < V_{IL}.
4. IIH is the input leakage current per I/O pin over recommended operating conditions V_{IH} < V_{IN} < VCCI. Input current is larger when operating outside recommended ranges.

Timing Characteristics

Table 2-41 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
4 mA	Std.	0.66	7.66	0.04	1.02	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	0.86	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.76	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
6 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
8 mA	Std.	0.66	4.91	0.04	1.02	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	0.86	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.76	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
12 mA	Std.	0.66	3.53	0.04	1.02	0.43	3.60	2.82	3.21	3.58	5.83	5.06	ns
	–1	0.56	3.00	0.04	0.86	0.36	3.06	2.40	2.73	3.05	4.96	4.30	ns
	–2	0.49	2.64	0.03	0.76	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
16 mA	Std.	0.66	3.33	0.04	1.02	0.43	3.39	2.56	3.26	3.68	5.63	4.80	ns
	–1	0.56	2.83	0.04	0.86	0.36	2.89	2.18	2.77	3.13	4.79	4.08	ns
	–2	0.49	2.49	0.03	0.76	0.32	2.53	1.91	2.44	2.75	4.20	3.58	ns
24 mA	Std.	0.66	3.08	0.04	1.02	0.43	3.13	2.12	3.32	4.06	5.37	4.35	ns
	–1	0.56	2.62	0.04	0.86	0.36	2.66	1.80	2.83	3.45	4.57	3.70	ns
	–2	0.49	2.30	0.03	0.76	0.32	2.34	1.58	2.48	3.03	4.01	3.25	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-54 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Standard I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 μA	2 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		–1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		–2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 μA	4 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		–1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		–2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 μA	6 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		–1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		–2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns
100 μA	8 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		–1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		–2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Timing Characteristics

Table 2-60 • 2.5 V LVC MOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	8.66	0.04	1.31	0.43	7.83	8.66	2.68	2.30	10.07	10.90	ns
	–1	0.51	7.37	0.04	1.11	0.36	6.66	7.37	2.28	1.96	8.56	9.27	ns
	–2	0.45	6.47	0.03	0.98	0.32	5.85	6.47	2.00	1.72	7.52	8.14	ns
6 mA	Std.	0.60	5.17	0.04	1.31	0.43	5.04	5.17	3.05	3.00	7.27	7.40	ns
	–1	0.51	4.39	0.04	1.11	0.36	4.28	4.39	2.59	2.55	6.19	6.30	ns
	–2	0.45	3.86	0.03	0.98	0.32	3.76	3.86	2.28	2.24	5.43	5.53	ns
8 mA	Std.	0.60	5.17	0.04	1.31	0.43	5.04	5.17	3.05	3.00	7.27	7.40	ns
	–1	0.51	4.39	0.04	1.11	0.36	4.28	4.39	2.59	2.55	6.19	6.30	ns
	–2	0.45	3.86	0.03	0.98	0.32	3.76	3.86	2.28	2.24	5.43	5.53	ns
12 mA	Std.	0.60	3.56	0.04	1.31	0.43	3.63	3.43	3.30	3.44	5.86	5.67	ns
	–1	0.51	3.03	0.04	1.11	0.36	3.08	2.92	2.81	2.92	4.99	4.82	ns
	–2	0.45	2.66	0.03	0.98	0.32	2.71	2.56	2.47	2.57	4.38	4.23	ns
16 mA	Std.	0.60	3.35	0.04	1.31	0.43	3.41	3.06	3.36	3.55	5.65	5.30	ns
	–1	0.51	2.85	0.04	1.11	0.36	2.90	2.60	2.86	3.02	4.81	4.51	ns
	–2	0.45	2.50	0.03	0.98	0.32	2.55	2.29	2.51	2.65	4.22	3.96	ns
24 mA	Std.	0.60	3.09	0.04	1.31	0.43	3.15	2.44	3.44	4.00	5.38	4.68	ns
	–1	0.51	2.63	0.04	1.11	0.36	2.68	2.08	2.92	3.40	4.58	3.98	ns
	–2	0.45	2.31	0.03	0.98	0.32	2.35	1.82	2.57	2.98	4.02	3.49	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-64 • 2.5 V LVCMOS High Slew

 Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
 Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	8.20	0.04	1.29	0.43	7.24	8.20	2.03	1.91	ns
	–1	0.56	6.98	0.04	1.10	0.36	6.16	6.98	1.73	1.62	ns
	–2	0.49	6.13	0.03	0.96	0.32	5.41	6.13	1.52	1.43	ns
4 mA	Std.	0.66	8.20	0.04	1.29	0.43	7.24	8.20	2.03	1.91	ns
	–1	0.56	6.98	0.04	1.10	0.36	6.16	6.98	1.73	1.62	ns
	–2	0.49	6.13	0.03	0.96	0.32	5.41	6.13	1.52	1.43	ns
6 mA	Std.	0.66	4.77	0.04	1.29	0.43	4.55	4.77	2.38	2.55	ns
	–1	0.56	4.05	0.04	1.10	0.36	3.87	4.05	2.03	2.17	ns
	–2	0.49	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns
8 mA	Std.	0.66	4.77	0.04	1.29	0.43	4.55	4.77	2.38	2.55	ns
	–1	0.56	4.05	0.04	1.10	0.36	3.87	4.05	2.03	2.17	ns
	–2	0.49	3.56	0.03	0.96	0.32	3.40	3.56	1.78	1.91	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-65 • 2.5 V LVCMOS Low Slew

 Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
 Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.00	0.04	1.29	0.43	10.37	11.00	2.03	1.83	ns
	–1	0.56	9.35	0.04	1.10	0.36	8.83	9.35	1.73	1.56	ns
	–2	0.49	8.21	0.03	0.96	0.32	7.75	8.21	1.52	1.37	ns
4 mA	Std.	0.66	11.00	0.04	1.29	0.43	10.37	11.00	2.03	1.83	ns
	–1	0.56	9.35	0.04	1.10	0.36	8.83	9.35	1.73	1.56	ns
	–2	0.49	8.21	0.03	0.96	0.32	7.75	8.21	1.52	1.37	ns
6 mA	Std.	0.66	7.50	0.04	1.29	0.43	7.36	7.50	2.39	2.46	ns
	–1	0.56	6.38	0.04	1.10	0.36	6.26	6.38	2.03	2.10	ns
	–2	0.49	5.60	0.03	0.96	0.32	5.49	5.60	1.78	1.84	ns
8 mA	Std.	0.66	7.50	0.04	1.29	0.43	7.36	7.50	2.39	2.46	ns
	–1	0.56	6.38	0.04	1.10	0.36	6.26	6.38	2.03	2.10	ns
	–2	0.49	5.60	0.03	0.96	0.32	5.49	5.60	1.78	1.84	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Timing Characteristics

Table 2-70 • 1.8 V LVC MOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.7\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	11.86	0.04	1.22	0.43	9.14	11.86	2.77	1.66	11.37	14.10	ns
	–1	0.56	10.09	0.04	1.04	0.36	7.77	10.09	2.36	1.41	9.67	11.99	ns
	–2	0.49	8.86	0.03	0.91	0.32	6.82	8.86	2.07	1.24	8.49	10.53	ns
4 mA	Std.	0.66	6.91	0.04	1.22	0.43	5.86	6.91	3.22	2.84	8.10	9.15	ns
	–1	0.56	5.88	0.04	1.04	0.36	4.99	5.88	2.74	2.41	6.89	7.78	ns
	–2	0.49	5.16	0.03	0.91	0.32	4.38	5.16	2.41	2.12	6.05	6.83	ns
6 mA	Std.	0.66	4.45	0.04	1.22	0.43	4.18	4.45	3.53	3.38	6.42	6.68	ns
	–1	0.56	3.78	0.04	1.04	0.36	3.56	3.78	3.00	2.88	5.46	5.69	ns
	–2	0.49	3.32	0.03	0.91	0.32	3.12	3.32	2.64	2.53	4.79	4.99	ns
8 mA	Std.	0.66	3.92	0.04	1.22	0.43	3.93	3.92	3.60	3.52	6.16	6.16	ns
	–1	0.56	3.34	0.04	1.04	0.36	3.34	3.34	3.06	3.00	5.24	5.24	ns
	–2	0.49	2.93	0.03	0.91	0.32	2.93	2.93	2.69	2.63	4.60	4.60	ns
12 mA	Std.	0.66	3.53	0.04	1.22	0.43	3.60	3.04	3.70	4.08	5.84	5.28	ns
	–1	0.56	3.01	0.04	1.04	0.36	3.06	2.59	3.15	3.47	4.96	4.49	ns
	–2	0.49	2.64	0.03	0.91	0.32	2.69	2.27	2.76	3.05	4.36	3.94	ns
16 mA	Std.	0.66	3.53	0.04	1.22	0.43	3.60	3.04	3.70	4.08	5.84	5.28	ns
	–1	0.56	3.01	0.04	1.04	0.36	3.06	2.59	3.15	3.47	4.96	4.49	ns
	–2	0.49	2.64	0.03	0.91	0.32	2.69	2.27	2.76	3.05	4.36	3.94	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-97 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OERMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OERMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IERMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-16 on page 2-71 for more information.

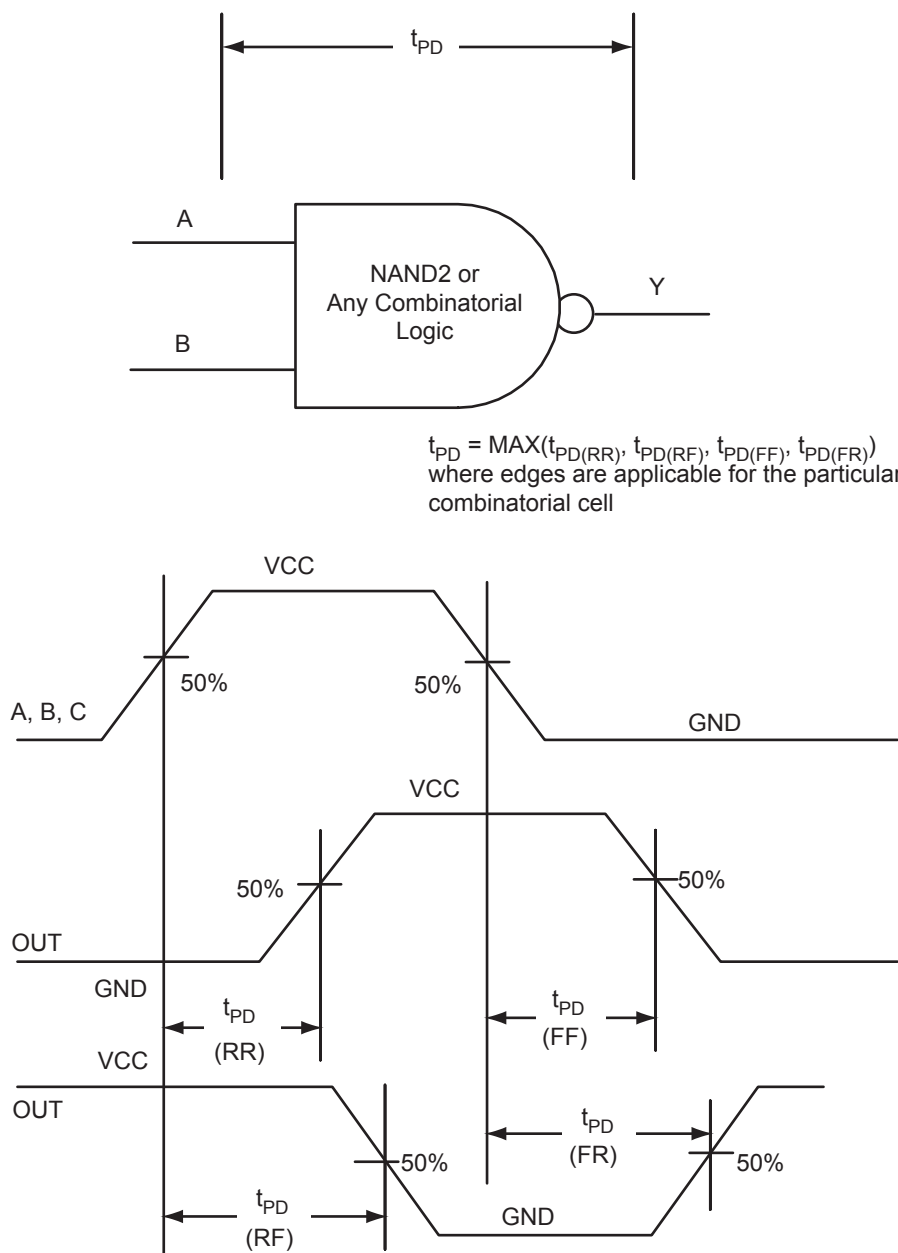


Figure 2-25 • Timing Model and Waveforms

Table 2-117 • RAM512X18**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$**

Parameter	Description	-2	-1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.13	0.15	0.17	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

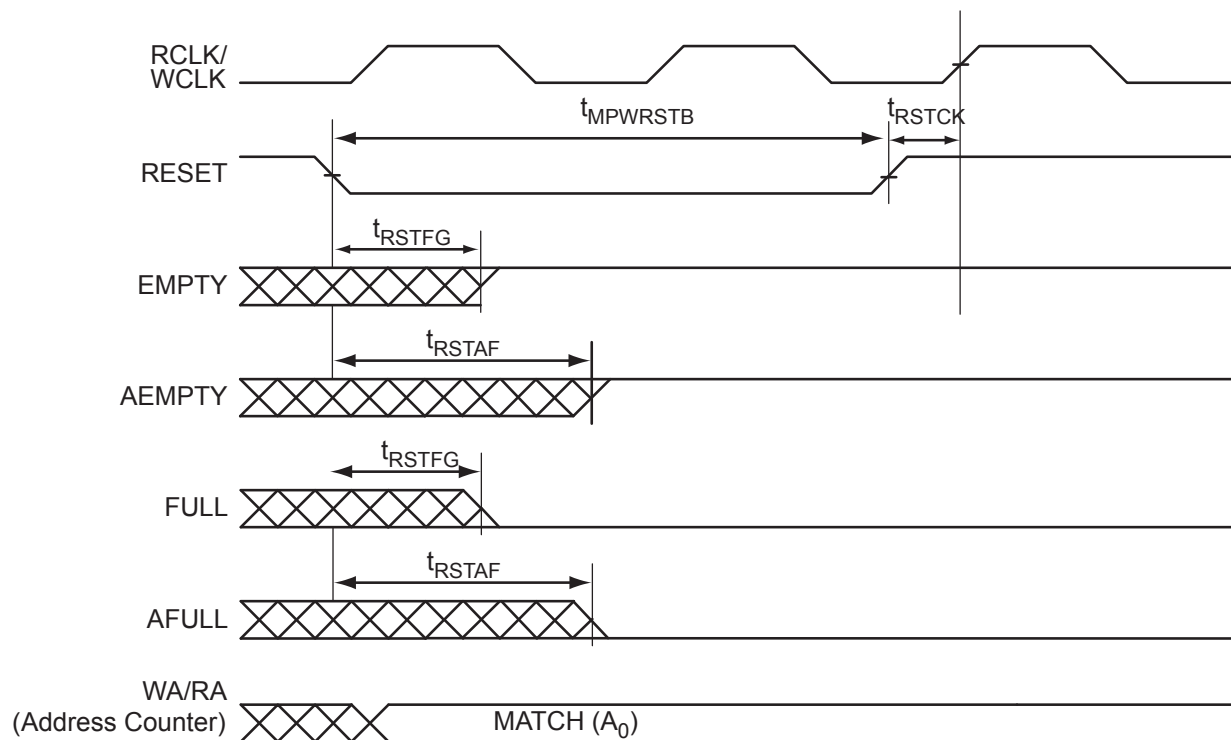


Figure 2-39 • FIFO Reset

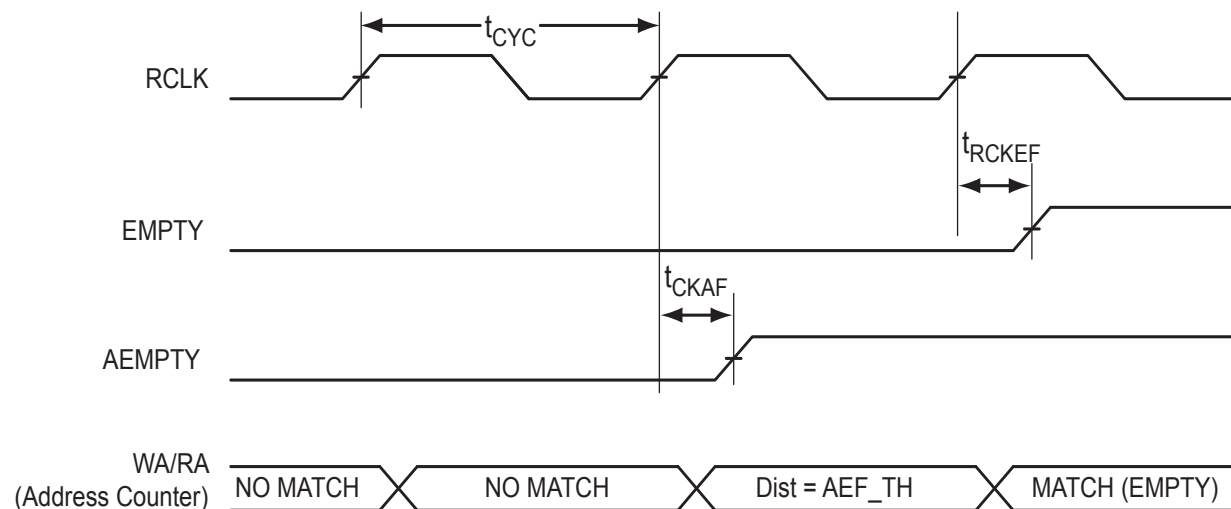


Figure 2-40 • FIFO EMPTY Flag and AEMPTY Flag Assertion

Table 2-121 • A3P250 FIFO 1k×4**Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$**

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.05	4.61	5.42	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	0.00	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
t_{REMRSTB}	RESET Removal	0.29	0.33	0.38	ns
t_{RECRSTB}	RESET Recovery	1.50	1.71	2.01	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency for FIFO	310	272	231	MHz

QN68	
Pin Number	A3P015 Function
1	IO82RSB1
2	IO80RSB1
3	IO78RSB1
4	IO76RSB1
5	GEC0/IO73RSB1
6	GEA0/IO72RSB1
7	GEB0/IO71RSB1
8	VCC
9	GND
10	VCCIB1
11	IO68RSB1
12	IO67RSB1
13	IO66RSB1
14	IO65RSB1
15	IO64RSB1
16	IO63RSB1
17	IO62RSB1
18	IO60RSB1
19	IO58RSB1
20	IO56RSB1
21	IO54RSB1
22	IO52RSB1
23	IO51RSB1
24	VCC
25	GND
26	VCCIB1
27	IO50RSB1
28	IO48RSB1
29	IO46RSB1
30	IO44RSB1
31	IO42RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP
36	TDO

QN68	
Pin Number	A3P015 Function
37	TRST
38	VJTAG
39	IO40RSB0
40	IO37RSB0
41	GDB0/IO34RSB0
42	GDA0/IO33RSB0
43	GDC0/IO32RSB0
44	VCCIB0
45	GND
46	VCC
47	IO31RSB0
48	IO29RSB0
49	IO28RSB0
50	IO27RSB0
51	IO25RSB0
52	IO24RSB0
53	IO22RSB0
54	IO21RSB0
55	IO19RSB0
56	IO17RSB0
57	IO15RSB0
58	IO14RSB0
59	VCCIB0
60	GND
61	VCC
62	IO12RSB0
63	IO10RSB0
64	IO08RSB0
65	IO06RSB0
66	IO04RSB0
67	IO02RSB0
68	IO00RSB0

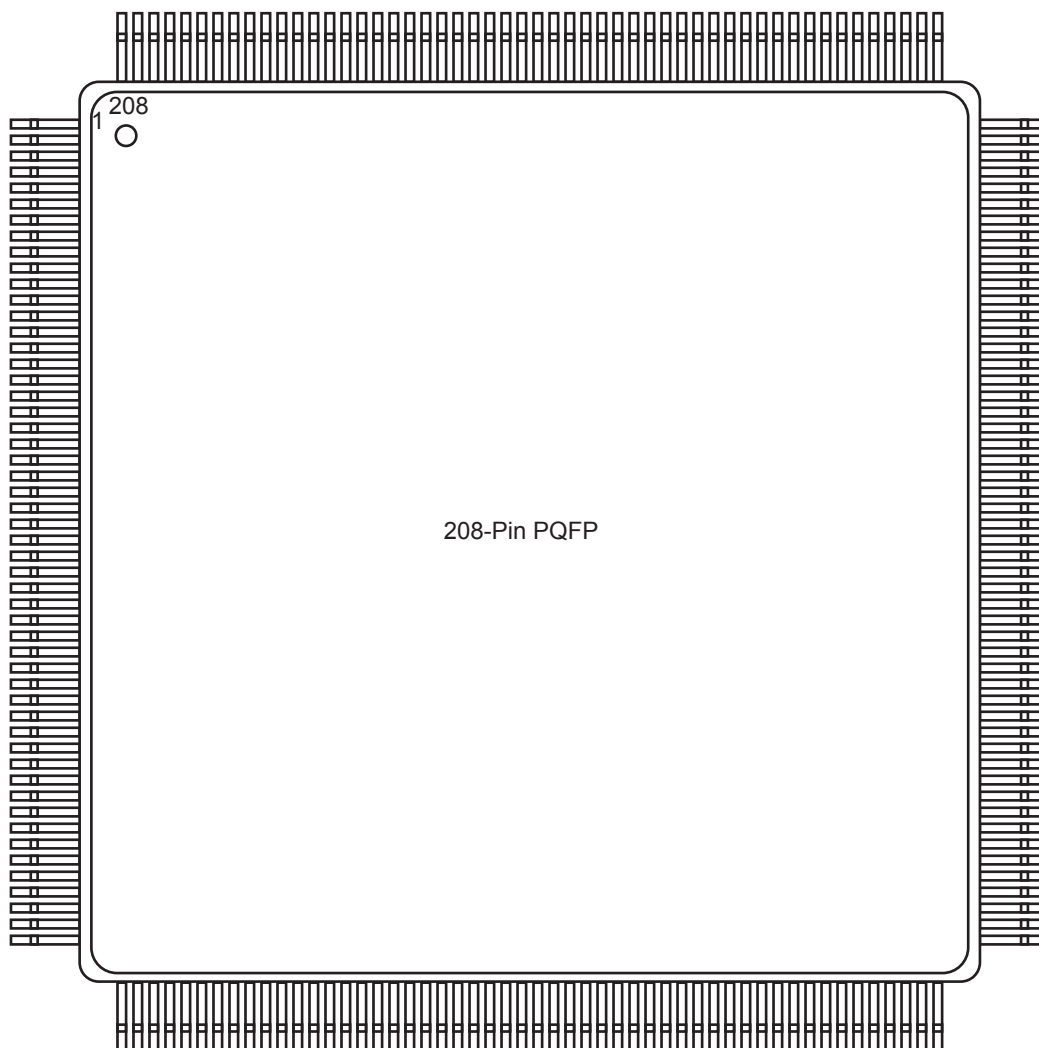
VQ100	
Pin Number	A3P125 Function
1	GND
2	GAA2/IO67RSB1
3	IO68RSB1
4	GAB2/IO69RSB1
5	IO132RSB1
6	GAC2/IO131RSB1
7	IO130RSB1
8	IO129RSB1
9	GND
10	GFB1/IO124RSB1
11	GFB0/IO123RSB1
12	VCOMPLF
13	GFA0/IO122RSB1
14	VCCPLF
15	GFA1/IO121RSB1
16	GFA2/IO120RSB1
17	VCC
18	VCCIB1
19	GEC0/IO111RSB1
20	GEB1/IO110RSB1
21	GEB0/IO109RSB1
22	GEA1/IO108RSB1
23	GEA0/IO107RSB1
24	VMV1
25	GNDQ
26	GEA2/IO106RSB1
27	GEB2/IO105RSB1
28	GEC2/IO104RSB1
29	IO102RSB1
30	IO100RSB1
31	IO99RSB1
32	IO97RSB1
33	IO96RSB1
34	IO95RSB1
35	IO94RSB1
36	IO93RSB1

VQ100	
Pin Number	A3P125 Function
37	VCC
38	GND
39	VCCIB1
40	IO87RSB1
41	IO84RSB1
42	IO81RSB1
43	IO75RSB1
44	GDC2/IO72RSB1
45	GDB2/IO71RSB1
46	GDA2/IO70RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO65RSB0
58	GDC0/IO62RSB0
59	GDC1/IO61RSB0
60	GCC2/IO59RSB0
61	GCB2/IO58RSB0
62	GCA0/IO56RSB0
63	GCA1/IO55RSB0
64	GCC0/IO52RSB0
65	GCC1/IO51RSB0
66	VCCIB0
67	GND
68	VCC
69	IO47RSB0
70	GBC2/IO45RSB0
71	GBB2/IO43RSB0
72	IO42RSB0

VQ100	
Pin Number	A3P125 Function
73	GBA2/IO41RSB0
74	VMV0
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO32RSB0
83	IO28RSB0
84	IO25RSB0
85	IO22RSB0
86	IO19RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	IO09RSB0
94	IO07RSB0
95	GAC1/IO05RSB0
96	GAC0/IO04RSB0
97	GAB1/IO03RSB0
98	GAB0/IO02RSB0
99	GAA1/IO01RSB0
100	GAA0/IO00RSB0

TQ144	
Pin Number	A3P125 Function
109	GBA1/IO40RSB0
110	GBA0/IO39RSB0
111	GBB1/IO38RSB0
112	GBB0/IO37RSB0
113	GBC1/IO36RSB0
114	GBC0/IO35RSB0
115	IO34RSB0
116	IO33RSB0
117	VCCIB0
118	GND
119	VCC
120	IO29RSB0
121	IO28RSB0
122	IO27RSB0
123	IO25RSB0
124	IO23RSB0
125	IO21RSB0
126	IO19RSB0
127	IO17RSB0
128	IO16RSB0
129	IO14RSB0
130	IO12RSB0
131	IO10RSB0
132	IO08RSB0
133	IO06RSB0
134	VCCIB0
135	GND
136	VCC
137	GAC1/IO05RSB0
138	GAC0/IO04RSB0
139	GAB1/IO03RSB0
140	GAB0/IO02RSB0
141	GAA1/IO01RSB0
142	GAA0/IO00RSB0
143	GNDQ
144	VMV0

PQ208 – Top View



Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

FG256	
Pin Number	A3P250 Function
G13	GCC1/IO48PPB1
G14	IO47NPB1
G15	IO54PDB1
G16	IO54NDB1
H1	GFB0/IO109NPB3
H2	GFA0/IO108NDB3
H3	GFB1/IO109PPB3
H4	VCOMPLF
H5	GFC0/IO110NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO48NPB1
H13	GCB1/IO49PPB1
H14	GCA0/IO50NPB1
H15	NC
H16	GCB0/IO49NPB1
J1	GFA2/IO107PPB3
J2	GFA1/IO108PDB3
J3	VCCPLF
J4	IO106NDB3
J5	GFB2/IO106PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO52PPB1
J13	GCA1/IO50PPB1
J14	GCC2/IO53PPB1
J15	NC
J16	GCA2/IO51PDB1

FG256	
Pin Number	A3P250 Function
K1	GFC2/IO105PDB3
K2	IO107NPB3
K3	IO104PPB3
K4	NC
K5	VCCIB3
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO52NPB1
K14	IO55RSB1
K15	IO53NPB1
K16	IO51NDB1
L1	IO105NDB3
L2	IO104NPB3
L3	NC
L4	IO102RSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO59VPB1
L14	IO57VDB1
L15	IO57UDB1
L16	IO56PDB1
M1	IO103PDB3
M2	NC
M3	IO101NPB3
M4	GEC0/IO100NPB3

FG256	
Pin Number	A3P250 Function
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	NC
M9	IO74RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	NC
M14	GDB1/IO59UPB1
M15	GDC1/IO58UDB1
M16	IO56NDB1
N1	IO103NDB3
N2	IO101PPB3
N3	GEC1/IO100PPB3
N4	NC
N5	GNDQ
N6	GEA2/IO97RSB2
N7	IO86RSB2
N8	IO82RSB2
N9	IO75RSB2
N10	IO69RSB2
N11	IO64RSB2
N12	GNDQ
N13	NC
N14	VJTAG
N15	GDC0/IO58VDB1
N16	GDA1/IO60UDB1
P1	GEB1/IO99PDB3
P2	GEB0/IO99NDB3
P3	NC
P4	NC
P5	IO92RSB2
P6	IO89RSB2
P7	IO85RSB2
P8	IO81RSB2

5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each version of the ProASIC3 datasheet.

Revision	Changes	Page
Revision 18 (March 2016)	Updated 3.3 V DC supply voltage's maximum Commercial and Industrial values from 3.3 V to 3.6 V in Table 2-2 (SAR 72693).	2-2
	Added reference of Package Mechanical Drawings document in all package pin assignment notes (76833).	NA
Revision 17 (June 2015)	Removed PQFP embedded heat spreader info. from Table 2-5 (SAR 52320).	2-6
	Updated " VCCIBx I/O Supply Voltage " (SAR 43323).	3-1
Revision 16 (December 2014)	Updated " ProASIC3 Ordering Information ". Interchanged the positions of Y- Security Feature and I- Application (Temperature Range) (SAR 61079). Added Note "Only devices with package size greater than or equal to 5x5 are supported".	1-IV
	Updated Table Note (2) in Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature so that the Table Note is not applicable for Maximum Storage Temperature T _{STG} (SAR 54297).	2-3
	Added values for Drive strength 2 mA in Table 2-41 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew , Table 2-42 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew , Table 2-43 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew , and Table 2-44 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew (SAR 57184).	2-34, 2-35, 2-36, 2-37
	Added Figure 2-1 • High-Temperature Data Retention (HTR) (SAR 45466).	2-3
	Updates made to maintain the style and consistency of the document.	NA
Revision 15 (July 2014)	Added corner pad table note (3) to " QN132 – Bottom View " (SAR 47442).	4-6
	Ambient temperature removed in Table 2-2 , table notes and " ProASIC3 Ordering Information " figure were modified (SAR 48343).	2-2 1-IV
	Other updates were made to maintain the style and consistency of the datasheet.	NA
Revision 14 (April 2014)	Note added for the discontinuance of QN132 package to the following tables and section: " ProASIC3 Devices ", " I/Os Per Package 1 ", " ProASIC3 FPGAs Package Sizes Dimensions " and " QN132 – Bottom View " section (SAR 55118).	I, III, 4-6

Revision	Changes	Page
Advance v0.2, (continued)	Table 2-43 was updated.	2-64
	Table 2-18 was updated.	2-45
	Pin descriptions in the "JTAG Pins" section were updated.	2-51
	The "User I/O Naming Convention" section was updated.	2-48
	Table 3-7 was updated.	3-6
	The "Methodology" section was updated.	3-10
	Table 3-40 and Table 3-39 were updated.	3-33,3-32
	The A3P250 "100-Pin VQFP*" pin table was updated.	4-14
	The A3P250 "208-Pin PQFP*" pin table was updated.	4-23
	The A3P1000 "208-Pin PQFP*" pin table was updated.	4-29
	The A3P250 "144-Pin FBGA*" pin table was updated.	4-36
	The A3P1000 "144-Pin FBGA*" pin table was updated.	4-32
	The A3P250 "256-Pin FBGA*" pin table was updated.	4-45
	The A3P1000 "256-Pin FBGA*" pin table was updated.	4-54
	The A3P1000 "484-Pin FBGA*" pin table was updated.	4-68